memory that has information specific to the respective pixels to allow individual corrections for those pixels. More specifically, where an electro-optical device has a point-defect pixel, signals corrected for that pixel are supplied to pixels around that pixel, to thereby cover the point defect, i.e., make it unrecognizable. Where a certain pixel is darker than pixels around it, a larger signal is supplied to that pixel to make the brightness of it be the same level as that of the adjacent pixels.

Page 28, first full paragraph:

(Amended) The central processing unit and the memory are of the same kinds as in an ordinary computer. In particular, the memory includes, as a RAM, an image memory corresponding to the respective pixels. Also, the intensity of back light which irradiates from the back side of the substrate can be changed in accordance with image information.

IN THE CLAIMS:

Please cancel claims 24-75 without prejudice or disclaimer to the subject matter disclosed therein.

Please amend claims 76-92 as follows:

76. (Amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
irradiating the semiconductor film with a laser light; and then
annealing the irradiated semiconductor film with a light; and then
patterning the semiconductor film to form at least one semiconductor island.

77. (Amended) A method according to claim 76 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

78. (Amended) A method according to claim 76 wherein said light is an infrared light.

79. (Amended) A method according to claim 76 further comprising a step of forming at

least channel, source, and drain regions in the semiconductor island layer of the semiconductor film by introducing impurities therein.

80. (Amended) A method of fabricating a semiconductor device comprising:
forming an insulating film on a substrate;
forming a semiconductor film on the insulating film;
irradiating the semiconductor film with a laser light; and then
annealing the irradiated semiconductor film with a light; and then
patterning the semiconductor film to form at least one semiconductor island.

81. (Amended) A method according to claim 80 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

82. (Amended) A method according to claim 80 wherein said light is an infrared light.

83. (Amended) A method according to claim 80 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island layer of the semiconductor film by introducing impurities therein.

84. (Amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
introducing a material comprising metal to the semiconductor film;
irradiating the semiconductor film with a laser light; then
annealing the irradiated semiconductor film with a light; and then
patterning the semiconductor film to form at least one semiconductor island.

85. (Amended) A method according to claim 84 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

86. (Amended) A method according to claim 84 wherein said light is an infrared light.

87. (Amended) A method according to claim 84 wherein said metal is at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag and Au.

88. (Amended) A method of fabricating a semiconductor device comprising:

forming a semiconductor film over a substrate having an insulating surface;

crystallizing the semiconductor film by a laser irradiation with a laser light; then

annealing the irradiated semiconductor film with a light so as to improve crystallinity of the semiconductor film;

heating the annealed semiconductor film in an atmosphere comprising nitrogen; and then

patterning the semiconductor film to form at least one semiconductor island.

89. (Amended) A method according to claim 88 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

90. (Amended) A method according to claim 88 wherein said light is an infrared light.

91. (Amended) A method according to claim 84 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island layer of the semiconductor film by introducing impurities therein.

92. (Amended) A method according to claim 88 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island layer of the semiconductor film by introducing impurities therein.

Please add the following new claims 93-102:

--93. (New) A method of fabricating a semiconductor device comprising:

forming a semiconductor film over a substrate having an insulating surface;

introducing a material comprising metal to the semiconductor film;

irradiating the semiconductor film with a laser light; then

annealing the irradiated semiconductor film with a light;

patterning the semiconductor film to form at least one semiconductor island; and

forming a gate insulating film over the semiconductor island.

94. (New) A method according to claim 93 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

95. (New) A method according to claim 93 wherein said light is an infrared light.

96. (New) A method according to claim 93 wherein said metal is at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag and Au.

97. (New) A method according to claim 93 further comprising a step of heating the annealed semiconductor film in an atmosphere comprising nitrogen.

97. (New) A method according to claim 93 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island layer of the semiconductor film by introducing impurities therein.

98. (New) A method according to claim 76, wherein said semiconductor device comprises a CPU on the substrate.

99. (New) A method according to claim 80, wherein said semiconductor device comprises a CPU on the substrate.

100. (New) A method according to claim 84, wherein said semiconductor device is used in a CPU on the substrate.

101. (New) A method according to claim 88, wherein said semiconductor device